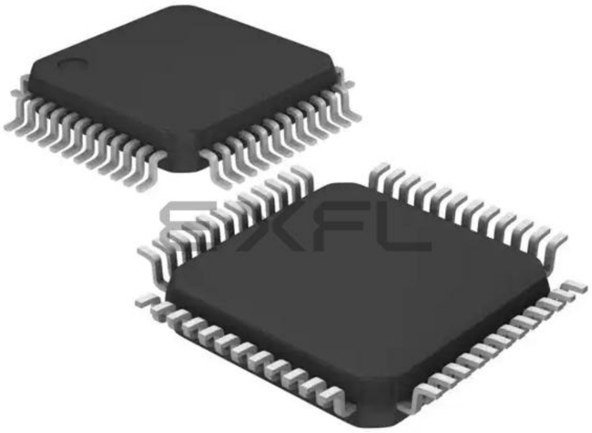


What is "Embedded - Microcontrollers"?

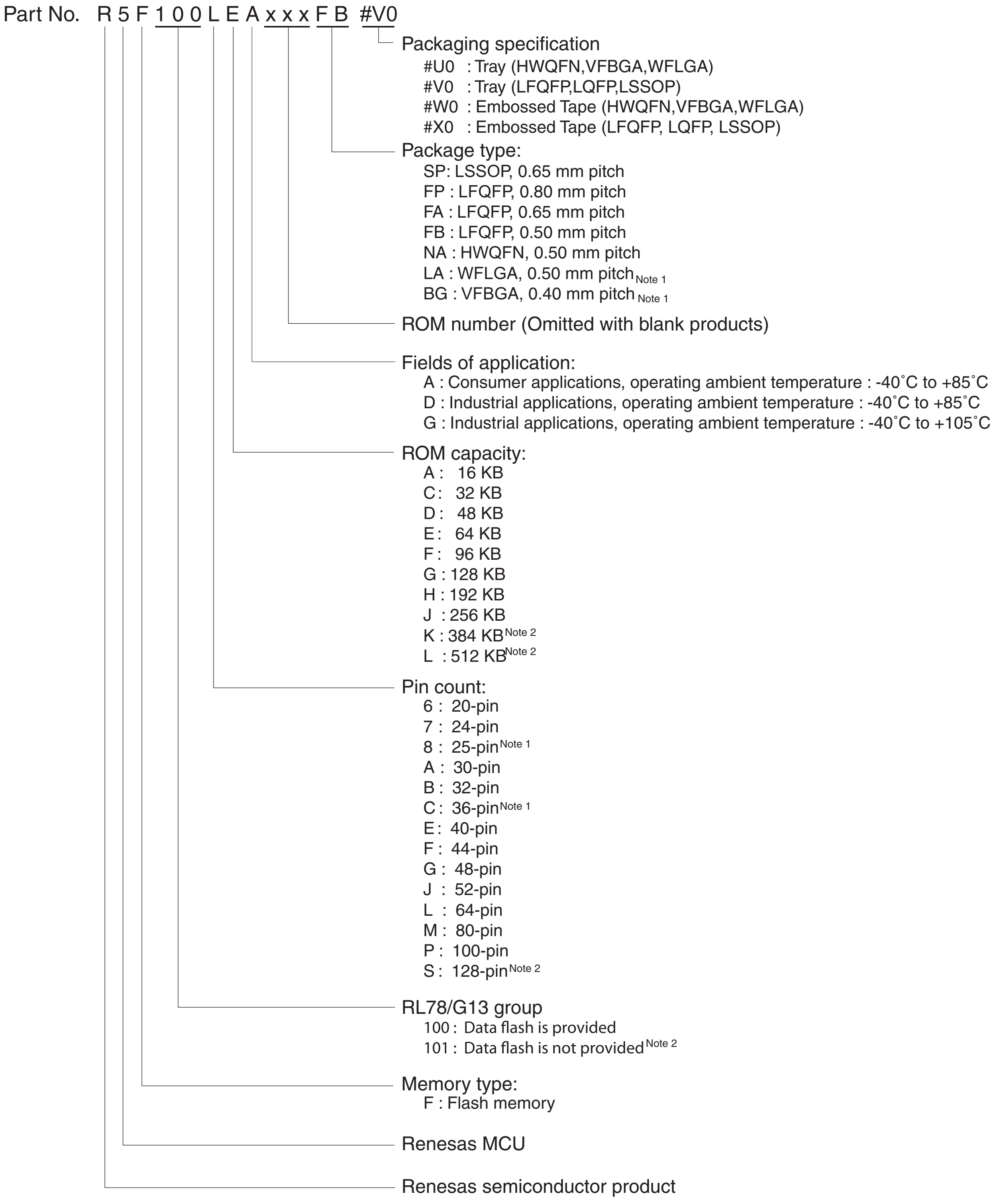
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101gcdfb-v0

1.2 List of Part Numbers

Figure 1-1. Part Number, Memory Size, and Package of RL78/G13



Part No. R 5 F 1 0 0 L E A x x x F B #V0

Packaging specification
#U0 : Tray (HWQFN,VFBGA,WFLGA)
#V0 : Tray (LFQFP,LQFP,LSSOP)
#W0 : Embossed Tape (HWQFN,VFBGA,WFLGA)
#X0 : Embossed Tape (LFQFP, LQFP, LSSOP)

Package type:
SP: LSSOP, 0.65 mm pitch
FP : LFQFP, 0.80 mm pitch
FA : LFQFP, 0.65 mm pitch
FB : LFQFP, 0.50 mm pitch
NA : HWQFN, 0.50 mm pitch
LA : WFLGA, 0.50 mm pitch Note 1
BG : VFBGA, 0.40 mm pitch Note 1

ROM number (Omitted with blank products)

Fields of application:
A : Consumer applications, operating ambient temperature : -40˚C to +85˚C
D : Industrial applications, operating ambient temperature : -40˚C to +85˚C
G : Industrial applications, operating ambient temperature : -40˚C to +105˚C

ROM capacity:
A : 16 KB
C : 32 KB
D : 48 KB
E : 64 KB
F : 96 KB
G : 128 KB
H : 192 KB
J : 256 KB
K : 384 KB Note 2
L : 512 KB Note 2

Pin count:
6 : 20-pin
7 : 24-pin
8 : 25-pin Note 1
A : 30-pin
B : 32-pin
C : 36-pin Note 1
E : 40-pin
F : 44-pin
G : 48-pin
J : 52-pin
L : 64-pin
M : 80-pin
P : 100-pin
S : 128-pin Note 2

RL78/G13 group
100 : Data flash is provided
101 : Data flash is not provided Note 2

Memory type:
F : Flash memory

Renesas MCU

Renesas semiconductor product

Notes **1.** Products only for “A: Consumer applications (T_A = –40 to +85°C)”, and "G: Industrial applications (T_A = –40 to +105°C)"

2. Products only for “A: Consumer applications (T_A = –40 to +85°C)”, and "D: Industrial applications (T_A = –40 to +85°C)"

Table 1-1. List of Ordering Part Numbers

(9/12)

Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F100LCAFB#V0, R5F100LDAFB#V0, R5F100LEAFB#V0, R5F100LFAFB#V0, R5F100LGAFB#V0, R5F100LHAFB#V0, R5F100LJAFB#V0, R5F100LKAFB#V0, R5F100LLAFB#V0 R5F100LCAFB#X0, R5F100LDAFB#X0, R5F100LEAFB#X0, R5F100LFAFB#X0, R5F100LGAFB#X0, R5F100LHAFB#X0, R5F100LJAFB#X0, R5F100LKAFB#X0, R5F100LLAFB#X0
			D	R5F100LCDFB#V0, R5F100LDDFB#V0, R5F100LEDFB#V0, R5F100LFDFB#V0, R5F100LGDFB#V0, R5F100LHDFB#V0, R5F100LJDFB#V0, R5F100LKDFB#V0, R5F100LLDFB#V0 R5F100LCDFB#X0, R5F100LDDFB#X0, R5F100LEDFB#X0, R5F100LFDFB#X0, R5F100LGDFB#X0, R5F100LHDFB#X0, R5F100LJDFB#X0, R5F100LKDFB#X0, R5F100LLDFB#X0
			G	R5F100LCGFB#V0, R5F100LDGFB#V0, R5F100LEGFB#V0, R5F100LFGFB#V0 R5F100LCGFB#X0, R5F100LDGFB#X0, R5F100LEGFB#X0, R5F100LFGFB#X0 R5F100LGGFB#V0, R5F100LHGFB#V0, R5F100LJGFB#V0 R5F100LGGFB#X0, R5F100LHGFB#X0, R5F100LJGFB#X0
		Not mounted	A	R5F101LCAFB#V0, R5F101LDAFB#V0, R5F101LEAFB#V0, R5F101LFAFB#V0, R5F101LGAFB#V0, R5F101LHAFB#V0, R5F101LJAFB#V0, R5F101LKAFB#V0, R5F101LLAFB#V0 R5F101LCAFB#X0, R5F101LDAFB#X0, R5F101LEAFB#X0, R5F101LFAFB#X0, R5F101LGAFB#X0, R5F101LHAFB#X0, R5F101LJAFB#X0, R5F101LKAFB#X0, R5F101LLAFB#X0
			D	R5F101LCDFB#V0, R5F101LDDFB#V0, R5F101LEDFB#V0, R5F101LFDFB#V0, R5F101LGDFB#V0, R5F101LHDFB#V0, R5F101LJDFB#V0, R5F101LKDFB#V0, R5F101LLDFB#V0 R5F101LCDFB#X0, R5F101LDDFB#X0, R5F101LEDFB#X0, R5F101LFDFB#X0, R5F101LGDFB#X0, R5F101LHDFB#X0, R5F101LJDFB#X0, R5F101LKDFB#X0, R5F101LLDFB#X0
	64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)	Mounted	A	R5F100LCABG#U0, R5F100LDABG#U0, R5F100LEABG#U0, R5F100LFABG#U0, R5F100LGABG#U0, R5F100LHABG#U0, R5F100LJABG#U0 R5F100LCABG#W0, R5F100LDABG#W0, R5F100LEABG#W0, R5F100LFABG#W0, R5F100LGABG#W0, R5F100LHABG#W0, R5F100LJABG#W0
			G	R5F100LCGBG#U0, R5F100LDGBG#U0, R5F100LEGBG#U0, R5F100LFGBG#U0, R5F100LGGBG#U0, R5F100LHGBG#U0, R5F100LJGBG#U0 R5F100LCGBG#W0, R5F100LDGBG#W0, R5F100LEGBG#W0, R5F100LFGBG#W0, R5F100LGGBG#W0, R5F100LHGBG#W0, R5F100LJGBG#W0
		Not mounted	A	R5F101LCABG#U0, R5F101LDABG#U0, R5F101LEABG#U0, R5F101LFABG#U0, R5F101LGABG#U0, R5F101LHABG#U0, R5F101LJABG#U0 R5F101LCABG#W0, R5F101LDABG#W0, R5F101LEABG#W0, R5F101LFABG#W0, R5F101LGABG#W0, R5F101LHABG#W0, R5F101LJABG#W0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Table 1-1. List of Ordering Part Numbers

(12/12)

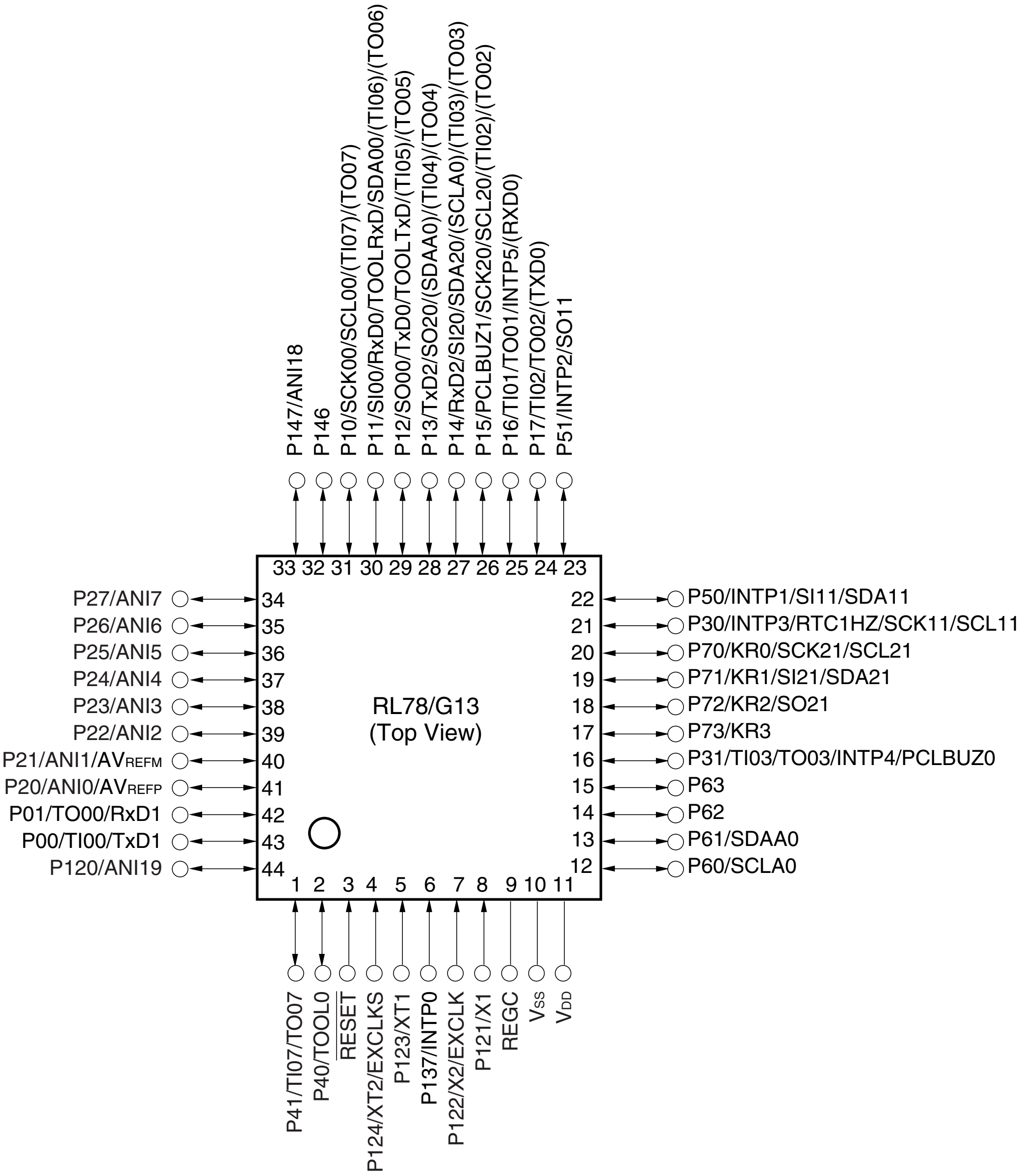
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0 R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0
			D	R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SLDFB#V0 R5F100SHDFB#X0, R5F100SJDFB#X0, R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	A	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0 R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0
			D	R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SJDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

Note For the fields of application, refer to **Figure 1-1 Part Number, Memory Size, and Package of RL78/G13**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3.8 44-pin products

- 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)

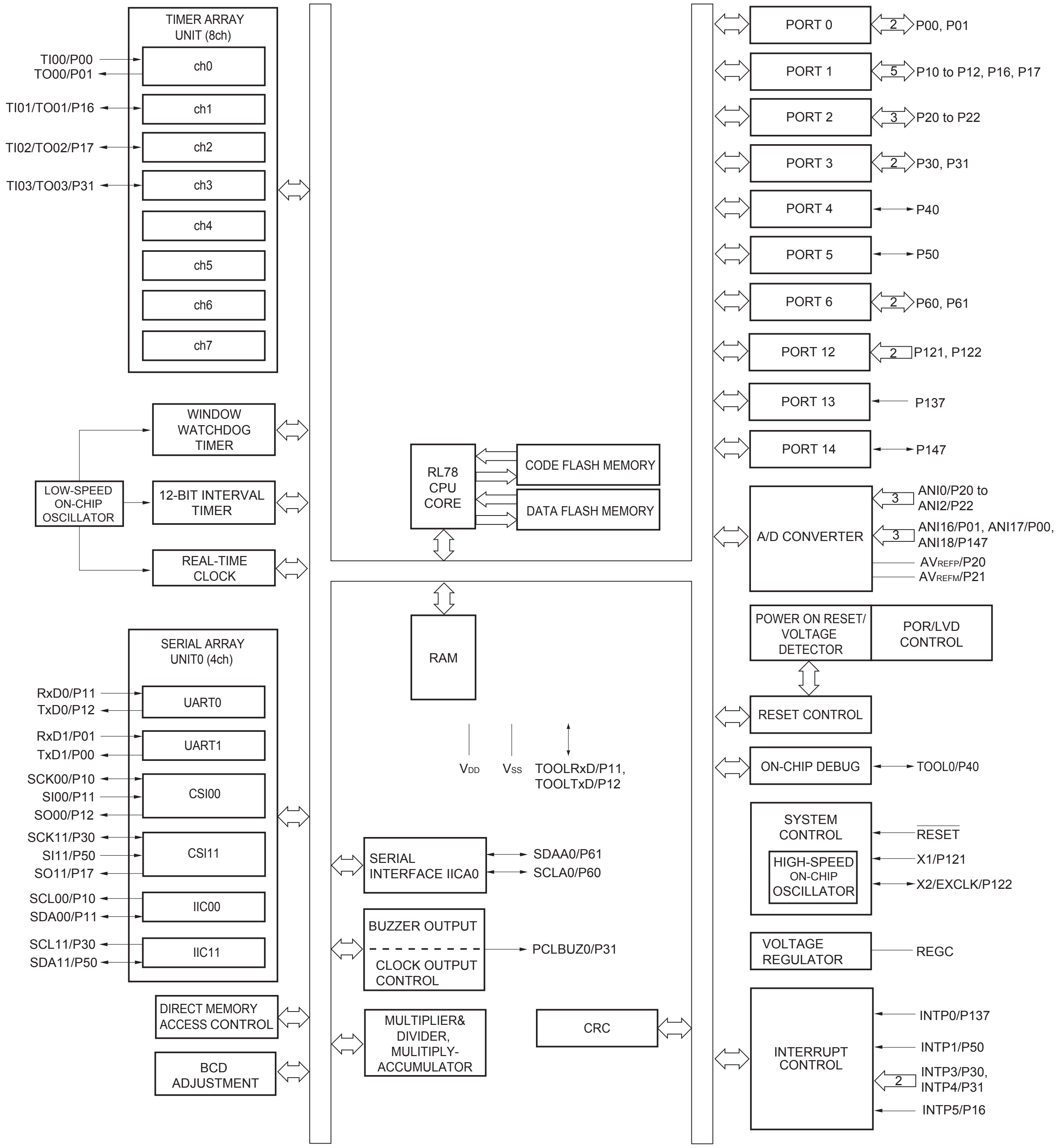


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF).

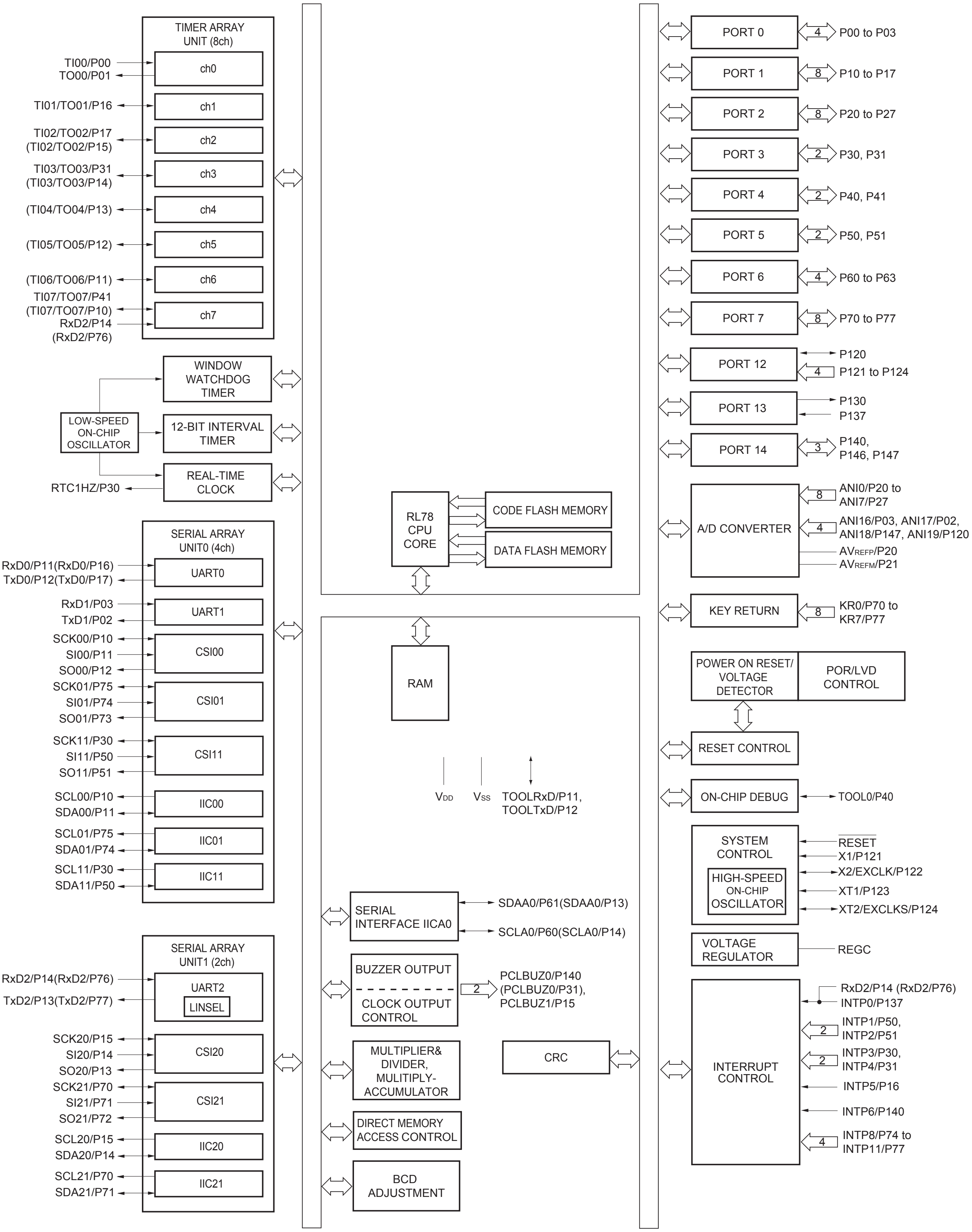
Remarks 1. For pin identification, see **1.4 Pin Identification**.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.2 24-pin products

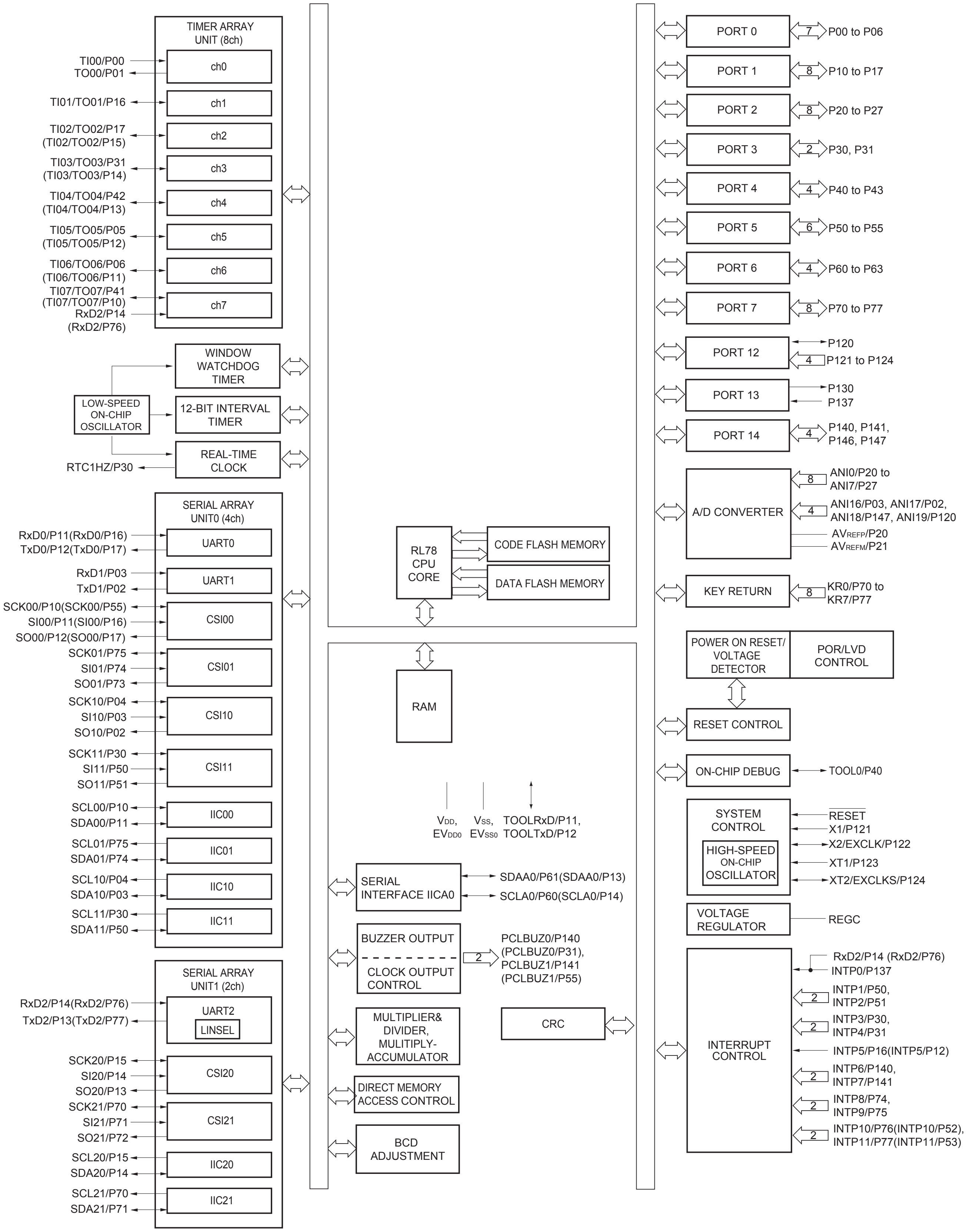


1.5.10 52-pin products



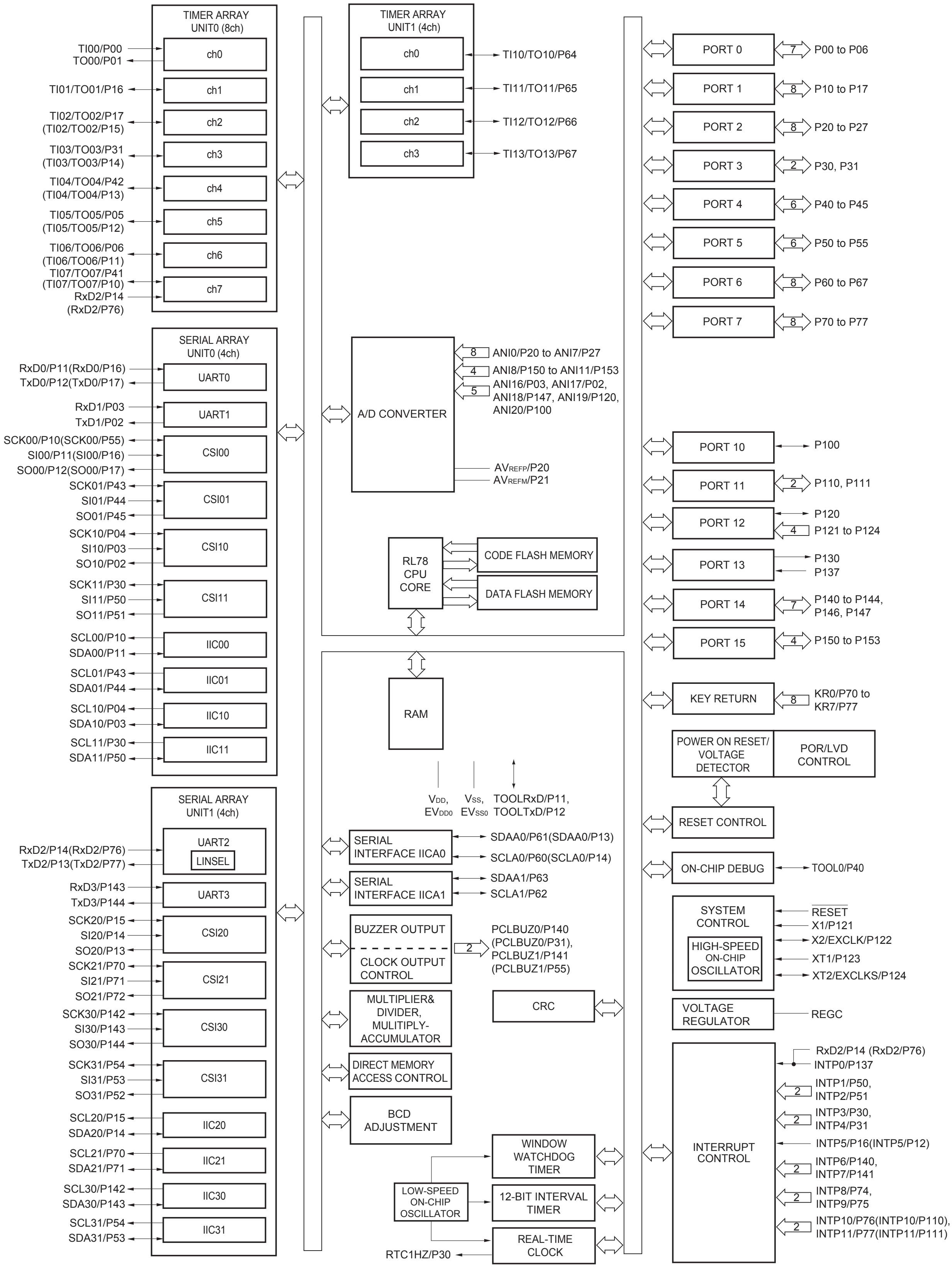
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.11 64-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.12 80-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

Item		80-pin		100-pin		128-pin	
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx
Code flash memory (KB)		96 to 512		96 to 512		192 to 512	
Data flash memory (KB)		8	–	8	–	8	–
RAM (KB)		8 to 32 Note 1		8 to 32 Note 1		16 to 32 Note 1	
Address space		1 MB					
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)					
	High-speed on-chip oscillator	HS (High-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)					
Subsystem clock		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz					
Low-speed on-chip oscillator		15 kHz (TYP.)					
General-purpose register		(8-bit register × 8) × 4 banks					
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator: f_{IH} = 32 MHz operation)					
		0.05 μs (High-speed system clock: f_{MX} = 20 MHz operation)					
		30.5 μs (Subsystem clock: f_{SUB} = 32.768 kHz operation)					
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.					
I/O port	Total	74		92		120	
	CMOS I/O	64 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 21)		82 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 24)		110 (N-ch O.D. I/O [EV_{DD} withstand voltage]: 25)	
	CMOS input	5		5		5	
	CMOS output	1		1		1	
	N-ch O.D. I/O (withstand voltage: 6 V)	4		4		4	
Timer	16-bit timer	12 channels		12 channels		16 channels	
	Watchdog timer	1 channel		1 channel		1 channel	
	Real-time clock (RTC)	1 channel		1 channel		1 channel	
	12-bit interval timer (IT)	1 channel		1 channel		1 channel	
	Timer output	12 channels (PWM outputs: 10 Note 2)		12 channels (PWM outputs: 10 Note 2)		16 channels (PWM outputs: 14 Note 2)	
	RTC output	1 channel • 1 Hz (subsystem clock: f_{SUB} = 32.768 kHz)					

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Notes 1. Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	$2.7\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 32 MHz
	$2.4\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 16 MHz
LS (low-speed main) mode:	$1.8\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 8 MHz
LV (low-voltage main) mode:	$1.6\ V \leq V_{DD} \leq 5.5\ V$@1 MHz to 4 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

Notes 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator and subsystem clock are stopped.

3. When high-speed system clock and subsystem clock are stopped.

4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.

5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V $\leq V_{DD} \leq$ 5.5 V@1 MHz to 32 MHz
2.4 V $\leq V_{DD} \leq$ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V $\leq V_{DD} \leq$ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V $\leq V_{DD} \leq$ 5.5 V@1 MHz to 4 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: High-speed on-chip oscillator clock frequency

3. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

(T_A = −40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD2} Note 2	HALT mode	HS (high-speed main) mode Note 7	f_{IH} = 32 MHz Note 4	V_{DD} = 5.0 V		0.62	1.89	mA
					V_{DD} = 3.0 V		0.62	1.89	mA
				f_{IH} = 24 MHz Note 4	V_{DD} = 5.0 V		0.50	1.48	mA
					V_{DD} = 3.0 V		0.50	1.48	mA
				f_{IH} = 16 MHz Note 4	V_{DD} = 5.0 V		0.44	1.12	mA
					V_{DD} = 3.0 V		0.44	1.12	mA
			LS (low-speed main) mode Note 7	f_{IH} = 8 MHz Note 4	V_{DD} = 3.0 V		290	620	μA
					V_{DD} = 2.0 V		290	620	μA
			LV (low-voltage main) mode Note 7	f_{IH} = 4 MHz Note 4	V_{DD} = 3.0 V		460	700	μA
					V_{DD} = 2.0 V		460	700	μA
			HS (high-speed main) mode Note 7	f_{MX} = 20 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.31	1.14	mA
					Resonator connection		0.48	1.34	mA
				f_{MX} = 20 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.31	1.14	mA
					Resonator connection		0.48	1.34	mA
				f_{MX} = 10 MHz Note 3, V_{DD} = 5.0 V	Square wave input		0.21	0.68	mA
					Resonator connection		0.28	0.76	mA
				f_{MX} = 10 MHz Note 3, V_{DD} = 3.0 V	Square wave input		0.21	0.68	mA
					Resonator connection		0.28	0.76	mA
			LS (low-speed main) mode Note 7	f_{MX} = 8 MHz Note 3, V_{DD} = 3.0 V	Square wave input		110	390	μA
					Resonator connection		160	450	μA
				f_{MX} = 8 MHz Note 3, V_{DD} = 2.0 V	Square wave input		110	390	μA
					Resonator connection		160	450	μA
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 5 T_A = −40°C	Square wave input		0.31	0.66	μA
					Resonator connection		0.50	0.85	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +25°C	Square wave input		0.38	0.66	μA
					Resonator connection		0.57	0.85	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +50°C	Square wave input		0.47	3.49	μA
					Resonator connection		0.66	3.68	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +70°C	Square wave input		0.80	6.10	μA
					Resonator connection		0.99	6.29	μA
				f_{SUB} = 32.768 kHz Note 5 T_A = +85°C	Square wave input		1.52	10.46	μA
					Resonator connection		1.71	10.65	μA
	I_{DD3} Note 6	STOP mode Note 8	T_A = −40°C				0.19	0.54	μA
			T_A = +25°C				0.26	0.54	μA
			T_A = +50°C				0.35	3.37	μA
			T_A = +70°C				0.68	5.98	μA
			T_A = +85°C				1.40	10.34	μA

(**Notes** and **Remarks** are listed on the next page.)

(5) During communication at same potential (simplified I^{2}C mode) (1/2)

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	$2.7\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 50$ pF, $R_b = 2.7$ kΩ		1000 Note 1		400 Note 1		400 Note 1	kHz
		$1.8\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 100$ pF, $R_b = 3$ kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		$1.8\ V \le EV_{DD0} < 2.7\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		$1.7\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ		250 Note 1		250 Note 1		250 Note 1	kHz
		$1.6\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ		—		250 Note 1		250 Note 1	kHz
Hold time when SCLr = “L”	t_{LOW}	$2.7\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 50$ pF, $R_b = 2.7$ kΩ	475		1150		1150		ns
		$1.8\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 100$ pF, $R_b = 3$ kΩ	1150		1150		1150		ns
		$1.8\ V \le EV_{DD0} < 2.7\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ	1550		1550		1550		ns
		$1.7\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ	1850		1850		1850		ns
		$1.6\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ	—		1850		1850		ns
Hold time when SCLr = “H”	t_{HIGH}	$2.7\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 50$ pF, $R_b = 2.7$ kΩ	475		1150		1150		ns
		$1.8\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 100$ pF, $R_b = 3$ kΩ	1150		1150		1150		ns
		$1.8\ V \le EV_{DD0} < 2.7\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ	1550		1550		1550		ns
		$1.7\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ	1850		1850		1850		ns
		$1.6\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100$ pF, $R_b = 5$ kΩ	—		1850		1850		ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

(5) During communication at same potential (simplified I^{2}C mode) (2/2)

($T_A = -40$ to $+85°C$, $1.6\ V \le EV_{DD0} = EV_{DD1} \le V_{DD} \le 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$)

Parameter	Symbol	Conditions	HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	$t_{SU:DAT}$	$2.7\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$	$1/f_{MCK} + 85$ Note2		$1/f_{MCK} + 145$ Note2		$1/f_{MCK} + 145$ Note2		ns
		$1.8\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 100\ pF$, $R_b = 3\ k\Omega$	$1/f_{MCK} + 145$ Note2		$1/f_{MCK} + 145$ Note2		$1/f_{MCK} + 145$ Note2		ns
		$1.8\ V \le EV_{DD0} < 2.7\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	$1/f_{MCK} + 230$ Note2		$1/f_{MCK} + 230$ Note2		$1/f_{MCK} + 230$ Note2		ns
		$1.7\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	$1/f_{MCK} + 290$ Note2		$1/f_{MCK} + 290$ Note2		$1/f_{MCK} + 290$ Note2		ns
		$1.6\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	—		$1/f_{MCK} + 290$ Note2		$1/f_{MCK} + 290$ Note2		ns
Data hold time (transmission)	$t_{HD:DAT}$	$2.7\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 50\ pF$, $R_b = 2.7\ k\Omega$	0	305	0	305	0	305	ns
		$1.8\ V \le EV_{DD0} \le 5.5\ V$, $C_b = 100\ pF$, $R_b = 3\ k\Omega$	0	355	0	355	0	355	ns
		$1.8\ V \le EV_{DD0} < 2.7\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	0	405	0	405	0	405	ns
		$1.7\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	0	405	0	405	0	405	ns
		$1.6\ V \le EV_{DD0} < 1.8\ V$, $C_b = 100\ pF$, $R_b = 5\ k\Omega$	—		0	405	0	405	ns

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

2. Set the f_{MCK} value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	24 MHz < f_{MCK}	14/f_{MCK}		—		—		ns
			20 MHz < f_{MCK} ≤ 24 MHz	12/f_{MCK}		—		—		ns
			8 MHz < f_{MCK} ≤ 20 MHz	10/f_{MCK}		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		—		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	24 MHz < f_{MCK}	20/f_{MCK}		—		—		ns
			20 MHz < f_{MCK} ≤ 24 MHz	16/f_{MCK}		—		—		ns
			16 MHz < f_{MCK} ≤ 20 MHz	14/f_{MCK}		—		—		ns
			8 MHz < f_{MCK} ≤ 16 MHz	12/f_{MCK}		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	8/f_{MCK}		16/f_{MCK}		—		ns
			f_{MCK} ≤ 4 MHz	6/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2	24 MHz < f_{MCK}	48/f_{MCK}		—		—		ns
			20 MHz < f_{MCK} ≤ 24 MHz	36/f_{MCK}		—		—		ns
			16 MHz < f_{MCK} ≤ 20 MHz	32/f_{MCK}		—		—		ns
			8 MHz < f_{MCK} ≤ 16 MHz	26/f_{MCK}		—		—		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		16/f_{MCK}		—		ns
			f_{MCK} ≤ 4 MHz	10/f_{MCK}		10/f_{MCK}		10/f_{MCK}		ns

(**Notes** and **Caution** are listed on the next page, and **Remarks** are listed on the page after the next page.)

2.5.2 Serial interface IICA

(1) I^2C standard mode

($T_A = -40$ to $+85°C$, $1.6\ V \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\ V$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\ V$)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Standard mode: $f_{CLK} \geq 1$ MHz	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$	0	100	0	100	0	100	kHz
			$1.8\ V \leq EV_{DD0} \leq 5.5\ V$	0	100	0	100	0	100	kHz
			$1.7\ V \leq EV_{DD0} \leq 5.5\ V$	0	100	0	100	0	100	kHz
			$1.6\ V \leq EV_{DD0} \leq 5.5\ V$	—		0	100	0	100	kHz
Setup time of restart condition	$t_{SU:STA}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.7		4.7		μs
Hold time[Note 1]	$t_{HD:STA}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.0		4.0		μs
Hold time when SCLA0 = "L"	t_{LOW}	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.7		4.7		μs
Hold time when SCLA0 = "H"	t_{HIGH}	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.0		4.0		μs
Data setup time (reception)	$t_{SU:DAT}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		250		250		250		ns
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		250		250		250		ns
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		250		250		250		ns
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		250		250		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		0	3.45	0	3.45	0	3.45	μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		0	3.45	0	3.45	0	3.45	μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		0	3.45	0	3.45	0	3.45	μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		0	3.45	0	3.45	μs
Setup time of stop condition	$t_{SU:STO}$	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.0		4.0		4.0		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.0		4.0		μs
Bus-free time	t_{BUF}	$2.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.8\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.7\ V \leq EV_{DD0} \leq 5.5\ V$		4.7		4.7		4.7		μs
		$1.6\ V \leq EV_{DD0} \leq 5.5\ V$		—		4.7		4.7		μs

(**Notes**, **Caution** and **Remark** are listed on the next page.)

(2) I^{2}C fast mode

(T_A = –40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: $f_{CLK} \geq 3.5$ MHz	2.7 V ≤ EV_{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
			1.8 V ≤ EV_{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart condition	$t_{SU:STA}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		0.6		0.6		0.6		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		0.6		0.6		0.6		µs
Hold time[Note 1]	$t_{HD:STA}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		0.6		0.6		0.6		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		0.6		0.6		0.6		µs
Hold time when SCLA0 = "L"	t_{LOW}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		1.3		1.3		1.3		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		1.3		1.3		1.3		µs
Hold time when SCLA0 = "H"	t_{HIGH}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		0.6		0.6		0.6		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		0.6		0.6		0.6		µs
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		100		100		100		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		100		100		100		µs
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		0	0.9	0	0.9	0	0.9	µs
Setup time of stop condition	$t_{SU:STO}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		0.6		0.6		0.6		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		0.6		0.6		0.6		µs
Bus-free time	t_{BUF}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		1.3		1.3		1.3		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		1.3		1.3		1.3		µs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

<R> **2.** The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: C_b = 320 pF, R_b = 1.1 kΩ

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)
(T_A = –40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	t_{KCY1}	t_{KCY1} ≥ 4/f_{CLK}	2.7 V ≤ EV_{DD0} ≤ 5.5 V	250		ns
			2.4 V ≤ EV_{DD0} ≤ 5.5 V	500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2 - 24$		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2 - 36$		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		$t_{KCY1}/2 - 76$		ns
SIp setup time (to SCKp↑) [Note 1]	t_{SIK1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V		66		ns
		2.7 V ≤ EV_{DD0} ≤ 5.5 V		66		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V		113		ns
SIp hold time (from SCKp↑) [Note 2]	t_{KSI1}			38		ns
Delay time from SCKp↓ to SOp output [Note 3]	t_{KSO1}	C = 30 pF [Note 4]			50	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

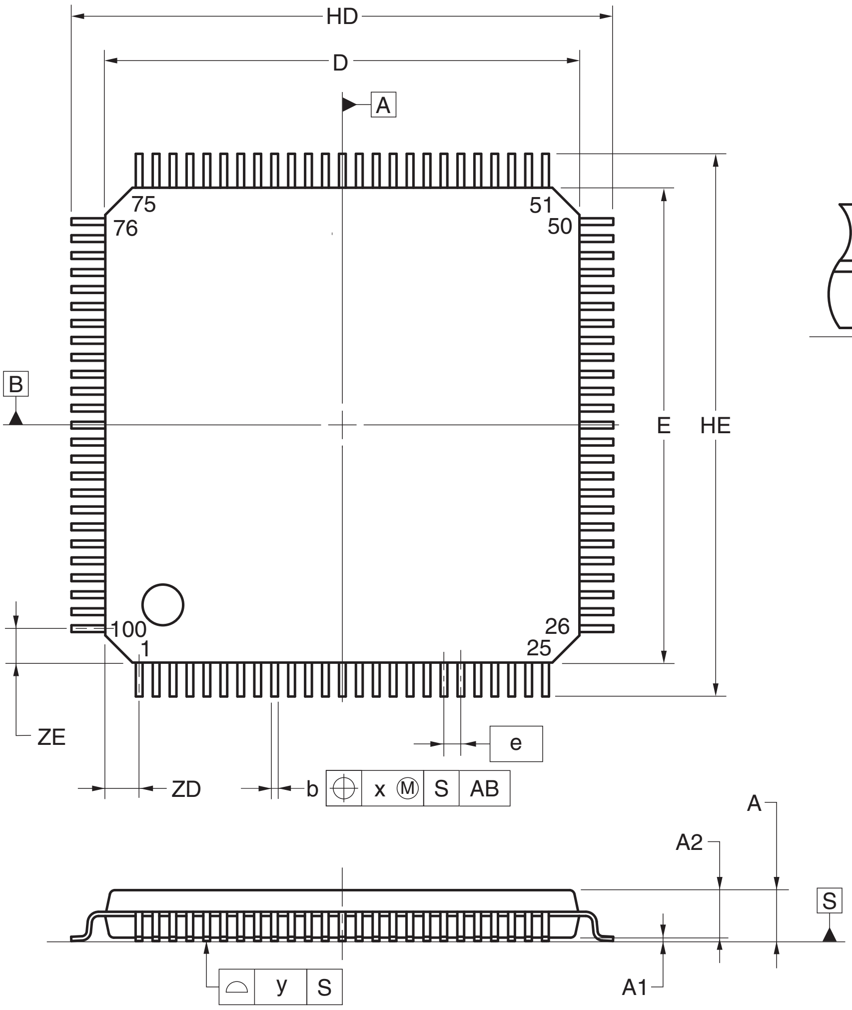
Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),
g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

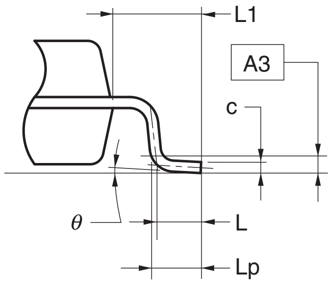
4.13 100-pin Products

R5F100PFAFB, R5F100PGAFB, R5F100PHAFB, R5F100PJAFB, R5F100PKAFB, R5F100PLAFB
R5F101PFAFB, R5F101PGAFB, R5F101PHAFB, R5F101PJAFB, R5F101PKAFB, R5F101PLAFB
R5F100PFDFB, R5F100PGDFB, R5F100PHDFB, R5F100PJDFB, R5F100PKDFB, R5F100PLDFB
R5F101PFDFB, R5F101PGDFB, R5F101PHDFB, R5F101PJDFB, R5F101PKDFB, R5F101PLDFB
R5F100PFGFB, R5F100PGGFB, R5F100PHGFB, R5F100PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	14.00±0.20
E	14.00±0.20
HD	16.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.22±0.05
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
e	0.50
x	0.08
y	0.08
ZD	1.00
ZE	1.00

Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
2. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
3. Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
4. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from such alteration, modification, copy or otherwise misappropriation of Renesas Electronics product.
5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.

   "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots etc.

   "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; and safety equipment etc.

   Renesas Electronics products are neither intended nor authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems, surgical implantations etc.), or may cause serious property damages (nuclear reactor control systems, military equipment etc.). You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application for which it is not intended. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for which the product is not intended by Renesas Electronics.
6. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
7. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or systems manufactured by you.
8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
9. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You should not use Renesas Electronics products or technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. When exporting the Renesas Electronics products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations.
10. It is the responsibility of the buyer or distributor of Renesas Electronics products, who distributes, disposes of, or otherwise places the product with a third party, to notify such third party in advance of the contents and conditions set forth in this document, Renesas Electronics assumes no responsibility for any losses incurred by you or third parties as a result of unauthorized use of Renesas Electronics products.
11. This document may not be reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.

(Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.

(Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

SALES OFFICES Renesas Electronics Corporation http://www.renesas.com

Refer to "http://www.renesas.com/" for the latest and detailed information.

California Eastern Laboratories, Inc.
4590 Patrick Henry Drive, Santa Clara, California 95054-1817, U.S.A.
Tel: +1-408-919-2500, Fax: +1-408-988-0279

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 1709, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100191, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.
No.777C, 100 Feet Road, HAL II Stage, Indiranagar, Bangalore, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.
12F., 234 Teheran-ro, Gangnam-Gu, Seoul, 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141

Colophon 5.0